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April 1st, 2010 Renesas Electronics Corporation

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2SK1628, 2SK1629

Silicon N Channel MOS FET

REJ03G0960-0400 Rev.4.00 May 13, 2009

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

RENESAS Package code: PRSS0004ZF-A (Package name: TO-3PL)

1. Gate 2. Drain 3. Source

Juc

γD

4

δs

				$(Ta = 25^{\circ}C)$	
Item		Symbol	Ratings	Unit	
Drain to source voltage	2SK1628	V _{DSS}	450	V	
	2SK1629		500		
Gate to source voltage		V _{GSS}	±30	V	
Drain current		I _D	30	А	
Drain peak current		I _{D(pulse)} * ¹	120	А	
Body to drain diode reverse d	rain current	I _{DR}	30	А	
Channel dissipation		Pch*2	200	W	
Channel temperature		Tch	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Notes: 1. $PW \le 10 \propto s$, duty cycle $\le 1\%$

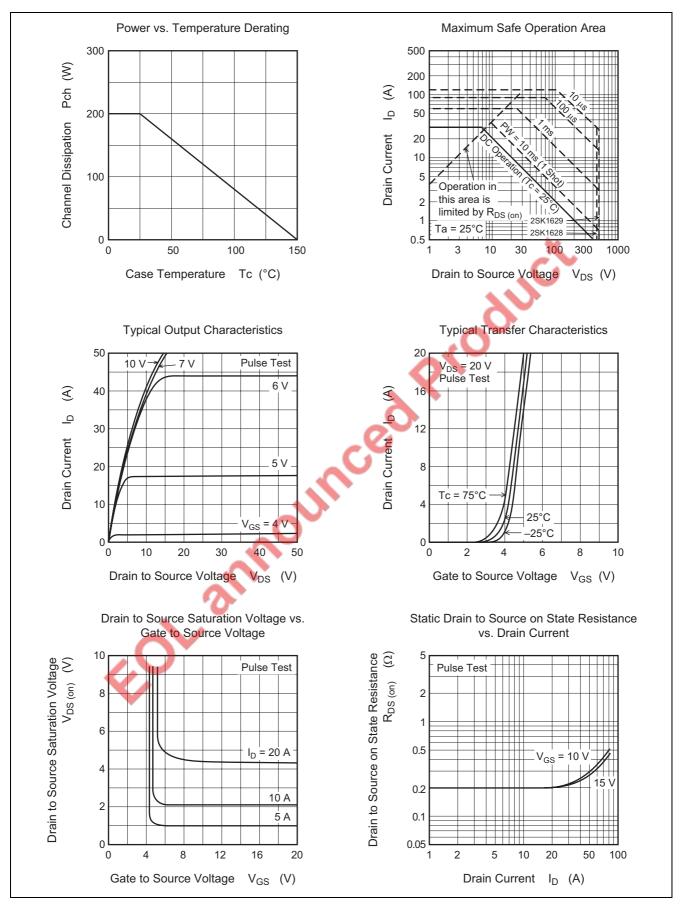
2. Value at $T_C = 25^{\circ}C$

Electrical Characteristics

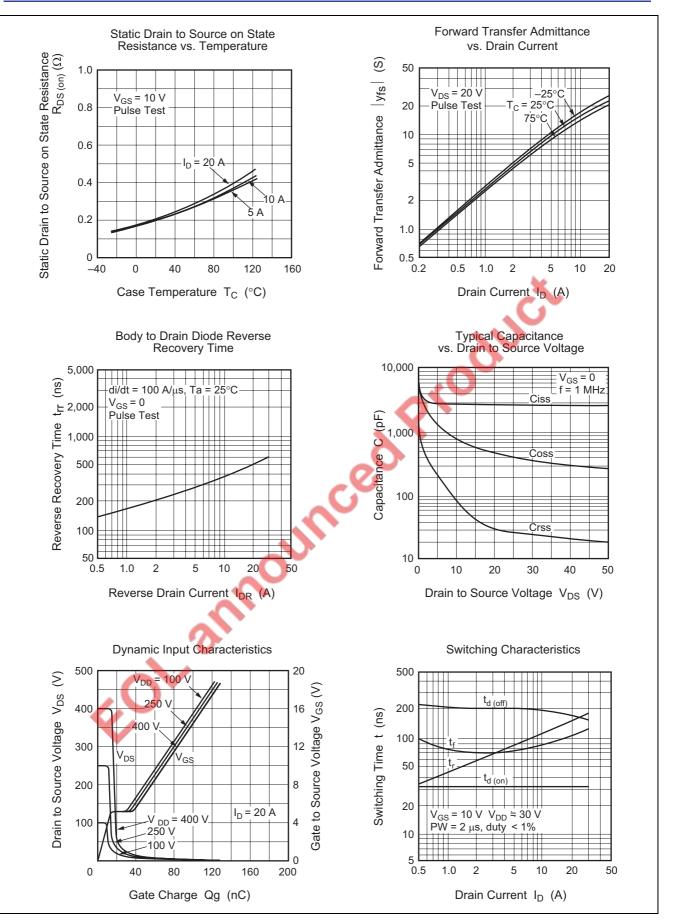
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	breakdown voltage $\overline{2SK1629}$ $\overline{500}$ $\overline{100}$ Gate to source breakdown voltage $V_{IBRIGSS}$ ± 30 $ V$ $I_G = \pm 100 \circ A, V_{DS} = 0$ Gate to source leak current I_{GSS} $ \pm 10$ $\circ A$ $V_{GS} = \pm 25$ $V, V_{DS} = 0$ Zero gate voltage drain $\underline{2SK1628}$ I_{DSS} $ 250$ $\circ A$ $V_{DS} = 360$ $V, V_{GS} = 0$ Current $\underline{2SK1629}$ V_{GS} 2.0 $ 3.0$ V $I_D = 1$ mA, $V_{DS} = 10$ $V_{DS} = 400$ $V_{CS} = 0$ Gate to source cutoff voltage $V_{GS(off)}$ 2.0 $ 3.0$ V $I_D = 1$ mA, $V_{DS} = 10$ $V_{CS} = 0$ Static drain to source on $\underline{2SK1629}$ $ 0.22$ 0.27 Ω $I_D = 15$ A, $V_{CS} = 10$ V^{-3} State resistance $\underline{2SK1629}$ $\underline{2SK1629}$ $ 0.22$ 0.27 Ω $I_D = 15$ A, $V_{CS} = 10$ V^{-3} Forward transfer admittance $ y_{15} $ 12 20 $-$ S $I_D = 15$ A, $V_{CS} = 10$ V^{-3} Input capacitance $Coss$ $ 780$ $ pF$ $V_{DS} = 10$ $V, V_{CS} = 0$ Output capacitance $Coss$ $ 780$ $ pF$ T	breakdown voltage Gate to source breakdown voltage Gate to source leak current Zero gate voltage drain current 2SK1628 2SK1629 Gate to source cutoff voltage Static drain to source on Static drain to source on State resistance State resistance State resistance 2SK1628 State resistance 2SK1629 Forward transfer admittance Input capacitance Output capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	V(BR)GSS IGSS IDSS VGS(off) RDS(on) [Vfs] Ciss COSS Crss Crss td(on) tr td(off) tf tf VDF	500 ±30 — 2.0 — 12 — 12 — 12 — — 12 — — 12 — — 12 — — 12 — —	 0.20 0.22 20 2800 780 90 32 140 200	±10 250 3.0 0.25 0.27 — — — — — — — — — — — — — — —	V ~A ~A V Ω S pF pF pF ns	$\begin{split} I_{G} &= \pm 100 \ \text{\simA, V_{DS} = 0$} \\ V_{GS} &= \pm 25 \ \text{V}, V_{DS} = 0 \\ V_{DS} &= 360 \ \text{V}, V_{GS} = 0 \\ V_{DS} &= 400 \ \text{V}, V_{GS} = 0 \\ I_{D} &= 1 \ \text{mA}, V_{DS} = 10 \ \text{V} \\ I_{D} &= 15 \ \text{A}, V_{GS} = 10 \ \text{V}^{*5} \\ V_{DS} &= 10 \ \text{V}, V_{GS} = 0, \\ f &= 1 \ \text{mHz} \\ I_{D} &= 15 \ \text{A}, V_{GS} = 10 \ \text{V}, \\ I_{D} &= 15 \ \text{A}, V_{GS} = 10 \ \text{V}^{*5} \\ \text{V}_{DS} &= 10 \ \text{V}, V_{GS} = 0, \\ f &= 1 \ \text{mHz} \\ I_{D} &= 15 \ \text{A}, V_{GS} = 10 \ \text{V}, \\ \end{array}$
Gate to source breakdown voltage $V_{(BR)GSS}$ ± 30 $ V$ $I_G = \pm 100 \approx A, V_{DS} = 0$ Gate to source leak current I_{GSS} $ \pm 10$ $\propto A$ $V_{GS} = \pm 25$ V, $V_{DS} = 0$ Zero gate voltage drain $2SK1628$ I_{DSS} $ \pm 10$ $\propto A$ $V_{GS} = \pm 25$ V, $V_{DS} = 0$ current $2SK1629$ I_{DSS} $ 250$ $\propto A$ $V_{DS} = 360$ V, $V_{GS} = 0$ Gate to source cutoff voltage $V_{GS(off)}$ 2.0 $ 3.0$ V $I_D = 1$ mA, $V_{DS} = 10$ VStatic drain to source on $2SK1628$ $R_{DS(on)}$ $ 0.20$ 0.25 Ω $I_D = 15$ A, $V_{GS} = 10$ VState resistance $2SK1629$ $ 0.22$ 0.27 Ω $I_D = 15$ A, $V_{GS} = 10$ VForward transfer admittance $ y_{1S} $ 12 20 $ S$ $I_D = 15$ A, $V_{GS} = 10$ VInput capacitanceCoss $ 780$ $ pF$ $V_{DS} = 10$ V, $V_{GS} = 0$ Output capacitanceCoss $ 780$ $ pF$ $f = 1$ MHzReverse transfer capacitanceCrss $ 90$ $ pF$ $I_D = 15$ A, $V_{GS} = 10$ V,Turn-off delay time $t_d(off)$ $ 200$ $ ns$ $I_D = 15$ A, $V_{GS} = 10$ V,Fall time t_f $ 1.00$ $ ns$ $I_P = 30$ A, $V_{GS} = 0$ Body to drain diode forward voltage V_{DF} $ 1.1$ <th>Gate to source breakdown voltage$V_{(BR)GSS}$$\pm 30VI_G = \pm 100 \text{ eA}, V_{DS} = 0$Gate to source leak current$I_{GSS}$$\pm 10$$\sim A$$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$Zero gate voltage drain$2SK1628$$I_{DSS}$$250$$\sim A$$V_{DS} = 360 \text{ V}, V_{GS} = 0$Current$2SK1629$$V_{CS}(off)$$2.0$-$3.0$$V$$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$Gate to source cutoff voltage$V_{CS}(off)$$2.0$-$3.0$$V$$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{S}$Static drain to source on$2SK1628$$R_{DS}(on)$-$0.22$$0.27$$\Omega$$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{S}$Forward transfer admittance$y_{IS}$$12$$20$-$S$$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{S}$Input capacitance$Ciss$-$2800$-$pF$$V_{DS} = 10 \text{ V}, V_{SS} = 0$Output capacitance$Ciss$-$2800$-$pF$$V_{DS} = 10 \text{ V}, V_{SS} = 0$Reverse transfer capacitance$Ciss$-90-$pF$$f = 1 \text{ MHz}$Reverse transfer capacitance$Cirss$-90-$pF$$f = 1 \text{ S}, V_{CS} = 10 \text{ V}, V_{CS} = 0$$I_D = 15 \text{ A}, V_{CS} = 10 \text{ V}, V_{CS} = 0$Body to drain diode forward voltageV_{D</th> <th>Gate to source breakdown voltage Gate to source leak current Zero gate voltage drain current 2SK1628 2SK1629 Gate to source cutoff voltage Static drain to source on Static drain to source on Static drain to source on Static drain to source on State resistance 2SK1628 2SK1629 Forward transfer admittance Input capacitance Output capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test</th> <th>I_{GSS} I_{DSS} V_{GS(off)} R_{DS(on)} y_{fs} Ciss Coss Crss t_d(on) t_r t_d(off) t_f V_{DF}</th> <th>±30 — 2.0 — 12 — — 12 — — — — — — — — — — — — —</th> <th> 0.20 0.22 20 2800 780 90 32 140 200</th> <th>±10 250 3.0 0.25 0.27 — — — — — — — — — — — — — — —</th> <th>∝A ∝A V Ω S pF pF pF ns</th> <th>$\begin{array}{l} V_{GS} = \pm 25 \ V, \ V_{DS} = 0 \\ V_{DS} = 360 \ V, \ V_{GS} = 0 \\ V_{DS} = 400 \ V, \ V_{GS} = 0 \\ I_D = 1 \ mA, \ V_{DS} = 10 \ V \\ I_D = 15 \ A, \ V_{GS} = 10 \ V \\ \end{array} \\ \begin{array}{l} \downarrow \\ I_D = 15 \ A, \ V_{DS} = 10 \ V \\ V_{DS} = 10 \ V, \ V_{GS} = 0, \\ f = 1 \ MHz \\ \end{array} \\ \begin{array}{l} I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \end{array}$</th>	Gate to source breakdown voltage $V_{(BR)GSS}$ ± 30 V $I_G = \pm 100 \text{ eA}, V_{DS} = 0$ Gate to source leak current I_{GSS} ± 10 $\sim A$ $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$ Zero gate voltage drain $2SK1628$ I_{DSS} 250 $\sim A$ $V_{DS} = 360 \text{ V}, V_{GS} = 0$ Current $2SK1629$ $V_{CS}(off)$ 2.0 - 3.0 V $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ Gate to source cutoff voltage $V_{CS}(off)$ 2.0 - 3.0 V $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{S}$ Static drain to source on $2SK1628$ $R_{DS}(on)$ - 0.22 0.27 Ω $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{S}$ Forward transfer admittance $ y_{IS} $ 12 20 - S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{S}$ Input capacitance $Ciss$ - 2800 - pF $V_{DS} = 10 \text{ V}, V_{SS} = 0$ Output capacitance $Ciss$ - 2800 - pF $V_{DS} = 10 \text{ V}, V_{SS} = 0$ Reverse transfer capacitance $Ciss$ - 90 - pF $f = 1 \text{ MHz}$ Reverse transfer capacitance $Cirss$ - 90 - pF $f = 1 \text{ S}, V_{CS} = 10 \text{ V}, V_{CS} = 0$ $I_D = 15 \text{ A}, V_{CS} = 10 \text{ V}, V_{CS} = 0$ Body to drain diode forward voltage V_{D	Gate to source breakdown voltage Gate to source leak current Zero gate voltage drain current 2SK1628 2SK1629 Gate to source cutoff voltage Static drain to source on Static drain to source on Static drain to source on Static drain to source on State resistance 2SK1628 2SK1629 Forward transfer admittance Input capacitance Output capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	I _{GSS} I _{DSS} V _{GS(off)} R _{DS(on)} y _{fs} Ciss Coss Crss t _d (on) t _r t _d (off) t _f V _{DF}	±30 — 2.0 — 12 — — 12 — — — — — — — — — — — — —	 0.20 0.22 20 2800 780 90 32 140 200	±10 250 3.0 0.25 0.27 — — — — — — — — — — — — — — —	∝A ∝A V Ω S pF pF pF ns	$ \begin{array}{l} V_{GS} = \pm 25 \ V, \ V_{DS} = 0 \\ V_{DS} = 360 \ V, \ V_{GS} = 0 \\ V_{DS} = 400 \ V, \ V_{GS} = 0 \\ I_D = 1 \ mA, \ V_{DS} = 10 \ V \\ I_D = 15 \ A, \ V_{GS} = 10 \ V \\ \end{array} \\ \begin{array}{l} \downarrow \\ I_D = 15 \ A, \ V_{DS} = 10 \ V \\ V_{DS} = 10 \ V, \ V_{GS} = 0, \\ f = 1 \ MHz \\ \end{array} \\ \begin{array}{l} I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \end{array} $
Gate to source leak currentIGSS ± 10 $\sim A$ $V_{GS} = \pm 25$ V, $V_{DS} = 0$ Zero gate voltage drain current $\frac{2SK1628}{2SK1629}$ Ibps250 $\sim A$ $\frac{V_{DS} = 360$ V, $V_{GS} = 0$ Gate to source cutoff voltage $V_{GS}(off)$ 2.0 3.0 VIb = 1 mA, $V_{DS} = 10$ VStatic drain to source on state resistance $2SK1628$ $P_{DS}(on)$ 0.20 0.25 Ω Ib = 15 A, $V_{GS} = 10$ VForward transfer admittance $ y_{fS} $ 12 20 SIb = 15 A, $V_{DS} = 10$ VInput capacitanceCiss 2800 pF $V_{DS} = 10$ V, $V_{GS} = 0$,Output capacitanceCoss 780 pF $V_{DS} = 10$ V, $V_{GS} = 0$,Turn-on delay timetd(on) 32 nsIb = 15 A, $V_{GS} = 10$ V,Rise timetr 140 nsRt = 2 Ω Turn-off delay timetd(off) 200 nsIF = 30 A, $V_{GS} = 0$,Body to drain diode forward voltage V_{DF} 1.1 VIF = 30 A, $V_{GS} = 0$,Body to drain diode reverse recoverytr 600 nsIF = 30 A, $V_{GS} = 0$,	Gate to source leak current Isss ± 10 $\sim A$ $V_{GS} = \pm 25$ V, $V_{DS} = 0$ Zero gate voltage drain current 2SK1628 Ibbs 250 $\sim A$ $V_{DS} = 360$ V, $V_{GS} = 0$ Gate to source cutoff voltage Voltage V_{SS(off)} 2.0 3.0 V Ib = 1 mA, V_{DS} = 10 V Static drain to source on 2SK1628 Rbs(on) 0.22 0.25 Ω Ib = 15 A, V_{GS} = 10 V Static drain to source on 2SK1629 Point 0.22 0.27 Ib = 15 A, V_{GS} = 10 V State resistance Forward transfer admittance Iyis 12 20 S Ib = 15 A, V_{GS} = 10 V State resistance Ib = 15 A, V_{GS} = 0 Output capacitance Ciss 90 pF V_{DS} = 10 V, V_{GS} = 0 Output capacitance Crss - 90 pF Turn-ont delay time ta(on) - 32 ns Ib = 15 A, V_{GS} = 10 V, State 10 V, State 10 V, State 10 V,	Gate to source leak current 2SK1628 Zero gate voltage drain current 2SK1628 Gate to source cutoff voltage 2SK1629 Gate to source cutoff voltage 2SK1628 Static drain to source on state resistance 2SK1628 Porward transfer admittance 1 Input capacitance 0 Output capacitance 1 Reverse transfer capacitance 1 Turn-on delay time 1 Rise time 1 Turn-off delay time 1 Body to drain diode forward voltage 1 Body to drain diode reverse recovery time 1 Note: 3. Pulse test	I _{GSS} I _{DSS} V _{GS(off)} R _{DS(on)} y _{fs} Ciss Coss Crss t _d (on) t _r t _d (off) t _f V _{DF}	 2.0 12 	 0.20 0.22 20 2800 780 90 32 140 200	±10 250 3.0 0.25 0.27 — — — — — — — — — — — — — — —	∝A ∝A V Ω S pF pF pF ns	$ \begin{array}{l} V_{GS} = \pm 25 \ V, \ V_{DS} = 0 \\ V_{DS} = 360 \ V, \ V_{GS} = 0 \\ V_{DS} = 400 \ V, \ V_{GS} = 0 \\ I_D = 1 \ mA, \ V_{DS} = 10 \ V \\ I_D = 15 \ A, \ V_{GS} = 10 \ V \\ \end{array} \\ \begin{array}{l} \downarrow \\ I_D = 15 \ A, \ V_{DS} = 10 \ V \\ V_{DS} = 10 \ V, \ V_{GS} = 0, \\ f = 1 \ MHz \\ \end{array} \\ \begin{array}{l} I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \end{array} $
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Zero gate voltage drain $2SK1628$ l_{DSS} 250 $\sim A$ $V_{DS} = 360 \text{ V}, V_{GS} = 0$ Gate to source cutoff voltage VGS(aff) 2.0 3.0 V $l_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ Static drain to source on $2SK1628$ $R_{DS(on)}$ 0.20 0.25 Ω $l_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+1}$ State resistance $2SK1629$ P_{DS} 12 20 S $l_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+1}$ Forward transfer admittance $ y_{fs} $ 12 20 S $l_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+1}$ Input capacitance Ciss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0$ Output capacitance Coss 780 pF $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}, V_{GS} = 0$ Turn-on delay time t_d(on) 32 ns $I_D = 16 \text{ A}, V_{GS} = 10 \text{ V}, V_{GS} = 0$ Rise time tr 140 ns $I_P = 30 \text{ A}, V_{GS} = 0$ <	Zero gate voltage drain current2SK1628 2SK1629Gate to source cutoff voltageSkit629Gate to source cutoff voltageStatic drain to source on state resistance2SK1628 2SK1629Forward transfer admittaCInput capacitanceInput capacitanceOutput capacitanceInput capacitanceTurn-on delay timeInput capacitanceFall timeInput capacitanceBody to drain diode forward voltageBody to drain diode reverse recovery timeNote:3. Pulse test	IDSS VGS(off) RDS(on) IVfs Ciss Coss Crss td(on) tr td(off) tf VDF		0.20 0.22 20 2800 780 90 32 140 200	250 3.0 0.25 0.27 -	∝A V Ω PF pF pF ns	
current2SK1629VDS = 400 V, VGS = 0Gate to source cutoff voltageVGS(off)2.0-3.0VIp = 1 mA, VDS = 10 VStatic drain to source on state resistance2SK1628 2SK1629RDS(on)-0.200.25 Ω Ib = 15 A, VGS = 10 VForward transfer admittance[yfs]1220-SIb = 15 A, VDS = 10 VVForward transfer admittance[yfs]1220-SIb = 15 A, VDS = 10 VVInput capacitanceCiss-2800-pFVDS = 10 V, VGS = 0,Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFf = 1 MHzTurn-on delay timetd(off)-32-nsIb = 15 A, VGS = 10 V,Rise timetr-140-nsRL = 2 Ω Turn-off delay timetd(off)-200-nsRL = 2 Ω Body to drain diode forward voltageVDF-1.1-VIF = 30 A, VGS = 0Body to drain diode reverse recoverytrr-600-nsIF = 30 A, VGS = 0, di (d A, VGS = 0, di	current 2SK1629 Vos = 400 V, Vos = 0 Gate to source cutoff voltage Vos (off) 2.0 - 3.0 V Ip = 1 mA, Vos = 10 V Static drain to source on 2SK1628 Rbs(on) - 0.20 0.25 Ω Ib = 15 A, Vos = 10 V State resistance 2SK1629 - 0.22 0.27 Ib = 15 A, Vos = 10 V Forward transfer admittance [yts] 12 20 - S Ib = 15 A, Vos = 10 V Input capacitance Ciss - 2800 - pF Vos = 10 V, Vos = 0 Output capacitance Ciss - 2800 - pF Vos = 10 V, Vos = 0 Output capacitance Coss - 780 - pF Vos = 10 V, Vos = 0 Reverse transfer capacitance Crss - 90 - pF Turn-on delay time ta(on) - 32 - ns Ib = 15 A, Vos = 10 V, Vos = 10 V	current2SK1629Gate to source cutoff voltageStatic drain to source on state resistance2SK1628 2SK1629Forward transfer admittanceInput capacitanceOutput capacitanceReverse transfer capacitanceTurn-on delay timeRise timeTurn-off delay timeFall timeBody to drain diode forward voltageBody to drain diode reverse recovery timeNote:3. Pulse test	VGS(off) RDS(on) IVfs Ciss Coss Crss td(on) tr td(off) tf VDF		0.20 0.22 20 2800 780 90 32 140 200	3.0 0.25 0.27 — — — — — — — — —	V Ω PF pF pF ns	$\label{eq:VDS} \hline V_{DS} = 400 \ V, \ V_{GS} = 0 \\ \hline I_D = 1 \ mA, \ V_{DS} = 10 \ V \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V \ ^{*0} \\ \hline I_D = 15 \ A, \ V_{DS} = 10 \ V \ ^{*0} \\ \hline V_{DS} = 10 \ V, \ V_{GS} = 0, \\ \hline f = 1 \ MHz \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 10 \ V, \\ \hline I_D = 15 \ A, \ V_{GS} = 10 \ V, \\ \hline I_D = 10 \ V, \\ \hline I_$
Gate to source cutoff voltage $V_{GS(off)}$ 2.03.0V $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$ Static drain to source on state resistance $2SK1628$ $2SK1629$ $R_{DS(on)}$ 0.200.25 $$ Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}$ Forward transfer admittance $2SK1629$ P_{T} 0.220.27 Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}$ Forward transfer admittance $Iy_{fs} $ 1220S $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}$ Input capacitanceCiss2800pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss780pFReverse transfer capacitanceCrss90pFTurn-on delay timetd(on)32ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr140ns $R_L = 2 \Omega$ Turn-off delay timetd(off)200ns $I_F = 30 \text{ A}, V_{GS} = 0$ Body to drain diode forward voltage V_{DF} 1.1V $I_F = 30 \text{ A}, V_{GS} = 0,$ Body to drain diode reverse recoverytrr600ns $I_F = 30 \text{ A}, V_{GS} = 0,$ diactracetrr600ns $I_F = 30 \text{ A}, V_{GS} = 0,$	Gate to source cutoff voltageVGS(off)2.0-3.0VIb = 1 mA, VDS = 10 VStatic drain to source on state resistance2SK1628RDS(on)-0.200.25 Ω Ib = 1 SA, VDS = 10 VForward transfer admittance[yts]1220-SIb = 15 A, VDS = 10 VVInput capacitanceCiss-2800-pFVDS = 10 V, VDS =	Gate to source cutoff voltage Static drain to source on state resistance 2SK1628 Static drain to source on state resistance 2SK1629 Forward transfer admittance Input capacitance Input capacitance 0utput capacitance Output capacitance 1 Turn-on delay time 1 Rise time 1 Turn-off delay time 1 Fall time 1 Body to drain diode forward voltage 1 Note: 3. Pulse test	RDS(on) Уfs Ciss Ciss Coss Crss Crss td(on) t tr td(off) tf VDF		0.20 0.22 20 2800 780 90 32 140 200	0.25 0.27 — — — — — — —	Ω S pF pF pF ns	$\begin{split} & I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V} \\ & I_D = 15 \text{ A}, V_{GS} = 10 \text{ V} \text{ *}^{10} \\ & I_D = 15 \text{ A}, V_{DS} = 10 \text{ V} \text{ *}^{10} \\ & V_{DS} = 10 \text{ V}, V_{GS} = 0, \\ & f = 1 \text{ MHz} \\ & I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}, \end{split}$
Static drain to source on state resistance $2SK1628$ $R_{DS(on)}$ 0.20 0.25 Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{*5}$ Forward transfer admittance $ y_{fs} $ 12 20 S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{*5}$ Input capacitance Ciss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitance Coss 780 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Reverse transfer capacitance Crss 90 pF $f = 1 \text{ MHz}$ Turn-on delay time td(on) 32 ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise time tr 140 ns $I_P = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Fall time tr 140 ns $I_P = 2 \Omega$ For the delay time tf 100 ns $I_F = 30 \text{ A}, V_{GS} = 0$ $I_P = 30 \text{ A}, V_{GS} = 0,$ $I_P = 30 \text{ A},$	Static drain to source on state resistance $2SK1628$ $2SK1629$ $R_{DS(on)}$ 0.20 0.25 0.27 Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{-5}$ Forward transfer admittance $ y_{1S} $ 12 20 S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{-5}$ Input capacitanceCiss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss 780 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Reverse transfer capacitanceCrss 90 pF $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-on delay time $t_{d(on)}$ 32 ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise time t_r 140 ns $I_P = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_{d(on)}$ 32 ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Fall time t_r 140 ns $I_P = 2 \Omega$ Body to drain diode forward voltage V_{DF} 1.1 V Body to drain diode reverse recovery t_{rr} 600 ns $I_F = 30 \text{ A}, V_{GS} = 0,$ Note: 3 . Pulse test V_{DF} 1.1 V $I_F = 30 \text{ A}, V_{GS} = 0,$	Static drain to source on state resistance2SK1628 2SK1629Forward transfer admittanceInput capacitanceInput capacitanceInput capacitanceOutput capacitanceInput capacitanceReverse transfer capacitanceInput capacitanceTurn-on delay timeInput capacitanceFall timeInput capacitanceBody to drain diode forward voltageInput capacitanceBody to drain diode reverse recovery timeInput capacitanceNote:3. Pulse test	RDS(on) Уfs Ciss Ciss Coss Crss Crss td(on) t tr td(off) tf VDF		0.20 0.22 20 2800 780 90 32 140 200	0.25 0.27 — — — — — — —	Ω S pF pF pF ns	$I_{D} = 15 \text{ A}, V_{GS} = 10 \text{ V} *$ $I_{D} = 15 \text{ A}, V_{DS} = 10 \text{ V} *$ $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$ $I_{D} = 15 \text{ A}, V_{GS} = 10 \text{ V},$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Static drain to source on state resistance 2SK1628 $R_{DS(on)}$ 0.20 0.25 Ω $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{-5}$ Forward transfer admittance Iyts 12 20 S $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{-5}$ Input capacitance Ciss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0$ Output capacitance Coss 780 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0$ Quiput capacitance Crss 90 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0$ Reverse transfer capacitance Crss 90 pF $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}, V_{GS} = 0$ Turn-on delay time $t_d(on)$ 32 ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}, V_{GS} = 10$	state resistance 2SK1629 Forward transfer admittance Input capacitance Output capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	RDS(on) Уfs Ciss Coss Crss td(on) tr td(off) tf VDF		0.22 20 2800 780 90 32 140 200	0.27 — — — — — — —	S pF pF pF ns	$\begin{split} & I_D = 15 \text{ A}, \text{ V}_{DS} = 10 \text{ V}^{*S} \\ & \text{V}_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \\ & \text{f} = 1 \text{ MHz} \\ & \text{I}_D = 15 \text{ A}, \text{ V}_{GS} = 10 \text{ V}, \end{split}$
state resistance $2SK1629$ — 0.22 0.27 Forward transfer admittance $ y_{fs} $ 12 20 —S $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+3}$ Input capacitanceCiss— 2800 —pF $V_{DS} = 10 \text{ V}, V_{GS} = 0$,Output capacitanceCoss— 780 —pF $f = 1 \text{ MHz}$ Reverse transfer capacitanceCrss— 90 —pFTurn-on delay time $t_{d(on)}$ — 32 —ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr— 140 —ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_{d(off)}$ — 200 —ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Fall timetr— 140 —ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Body to drain diode forward voltage V_{DF} — 1.1 — V Body to drain diode reverse recovery t_{rr} — 600 —ns $I_F = 30 \text{ A}, V_{GS} = 0,$ dia//dt $I_{OD} A/c_D$ I_{rr} — 600 —ns $I_F = 30 \text{ A}, V_{GS} = 0,$	state resistance 2SK1629 0.22 0.27 Forward transfer admittance $ y_{15} $ 12 20 S $I_0 = 15 \text{ A}, V_{DS} = 10 \text{ V}^{+3}$ Input capacitance Ciss 2800 pF $V_{DS} = 10 \text{ V}, V_{GS} = 0, V_{OS} = 0$ Output capacitance Ciss 780 pF $f = 1 \text{ MHz}$ Reverse transfer capacitance Crss 90 pF $f = 1 \text{ MHz}$ Turn-on delay time $t_{d(on)}$ 32 ns $I_0 = 15 \text{ A}, V_{GS} = 10 \text{ V}, V_{GS} = 10 \text{ V},$	Forward transfer admittanceInput capacitanceOutput capacitanceReverse transfer capacitanceTurn-on delay timeRise timeTurn-off delay timeFall timeBody to drain diode forward voltageBody to drain diode reverse recoverytimeNote:3. Pulse test	y _{fs} Ciss Coss Crss t _{d(on)} t _r t _{d(off)} t _f V _{DF}		20 2800 780 90 32 140 200		pF pF pF ns	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ f = 1 MHz $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Input capacitanceCiss-2800-pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFfTurn-on delay time $t_{d(on)}$ -32-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr-140-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_d(off)$ -200-nsFall timetr-100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recovery timetrr-600-nsNote:3. Pulse testImage: state	Input capacitanceOutput capacitanceReverse transfer capacitanceTurn-on delay timeRise timeTurn-off delay timeFall timeBody to drain diode forward voltageBody to drain diode reverse recoverytimeNote:3. Pulse test	Ciss Coss Crss td(on) tr td(off) tf VDF		2800 780 90 32 140 200	— — — —	pF pF pF ns	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ f = 1 MHz $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Input capacitanceCiss-2800-pF $V_{DS} = 10 \text{ V}, V_{GS} = 0,$ Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFfTurn-on delay time $t_{d(on)}$ -32-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr-140-ns $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Turn-off delay time $t_d(off)$ -200-nsFall timetr-100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recovery timetrr-600-nsNote:3. Pulse testImage: state	Output capacitanceReverse transfer capacitanceTurn-on delay timeRise timeTurn-off delay timeFall timeBody to drain diode forward voltageBody to drain diode reverse recoverytimeNote: 3. Pulse test	Ciss Coss Crss td(on) tr td(off) tf VDF	- - - -	780 90 32 140 200	— — — —	pF pF ns	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ f = 1 MHz $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Output capacitanceCoss-780-pFf = 1 MHzReverse transfer capacitanceCrss-90-pFTurn-on delay time $t_{d(on)}$ -32-ns $l_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise timetr-140-ns $P_L = 2 \Omega$ Turn-off delay time $t_{d(off)}$ -200-nsFall timetr-100-nsBody to drain diode forward voltage V_{DF} -1.1-VBody to drain diode reverse recoverytrr-600-nsImeNote:3. Pulse test-ns $I_F = 30 \text{ A}, V_{GS} = 0,$	Output capacitance Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	Coss Crss td(on) tr td(off) tf VDF		780 90 32 140 200		pF ns	f = 1 MHz $I_D = 15 \text{ A}, V_{GS} = 10 \text{ V},$
Reverse transfer capacitanceCrss90pFTurn-on delay time $t_{d(on)}$ 32nsI_D = 15 A, V_{GS} = 10 V,Rise time t_r 140nsR_L = 2 Ω Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery t_{rr} 600nsImage: time t_{rr} 600nsI_F = 30 A, V_{GS} = 0, div/dt = 100 A/c a	Reverse transfer capacitanceCrss90pFTurn-on delay time $t_{d(on)}$ 32ns $b = 15 \text{ A}, V_{GS} = 10 \text{ V},$ Rise time t_r 140ns $R_L = 2 \Omega$ Turn-off delay time $t_{d(off)}$ 200nsFall time t_f 100nsBody to drain diode forward voltage V_{DF} 1.1VBody to drain diode reverse recovery time t_{rr} 600nsNote:3. Pulse test	Reverse transfer capacitance Turn-on delay time Rise time Turn-off delay time Fall time Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	Crss td(on) tr td(off) tf VDF		32 140 200	—	pF ns	
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Body to drain diode forward voltage V_{DF} -1.1- $V_{IF} = 30 \text{ A}, V_{GS} = 0$ Body to drain diode reverse recovery t_{rr} -600ns $I_F = 30 \text{ A}, V_{GS} = 0,$ time t_{rr} -600- t_{rr} -	Body to drain diode forward voltage V_{DF} 1.1VIF = 30 A, V_{GS} = 0Body to drain diode reverse recovery time t_{rr} 600nsIF = 30 A, V_{GS} = 0, diF/dt = 100 A/~sNote:3. Pulse test	Body to drain diode forward voltage Body to drain diode reverse recovery time Note: 3. Pulse test	V _{DF}		100		ns	
Body to drain diode reverse recovery t_{rr} — 600 \leftarrow ns $I_F = 30 \text{ A}, V_{GS} = 0,$	Body to drain diode reverse recovery t_{rr} — 600 — ns $l_F = 30 \text{ A}, V_{GS} = 0, di_F/dt = 100 \text{ A}/\sim \text{s}$ Note: 3. Pulse test	Body to drain diode reverse recovery time Note: 3. Pulse test						$I_F = 30 \text{ A}, V_{GS} = 0$
time di _F /dt = 100 A/~s	Note: 3. Pulse test	Note: 3. Pulse test		_	600		ns	
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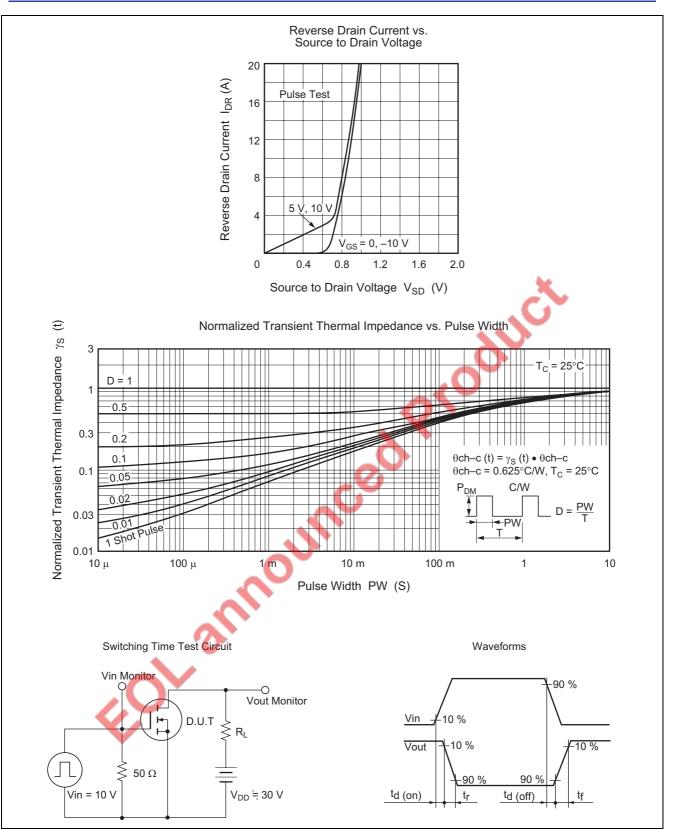
Main Characteristics



RENESAS

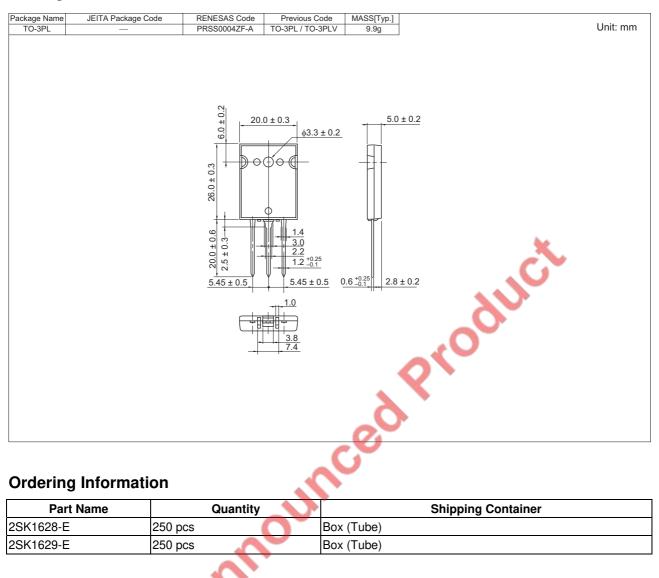


RENESAS



RENESAS

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container	
2SK1628-E	250 pcs	Box (Tube)	
2SK1629-E	250 pcs	Box (Tube)	
	31 an		

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